

Silicon NPN Power Transistors

2SC2542

DESCRIPTION

- With TO-220C package
- High voltage ,high speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

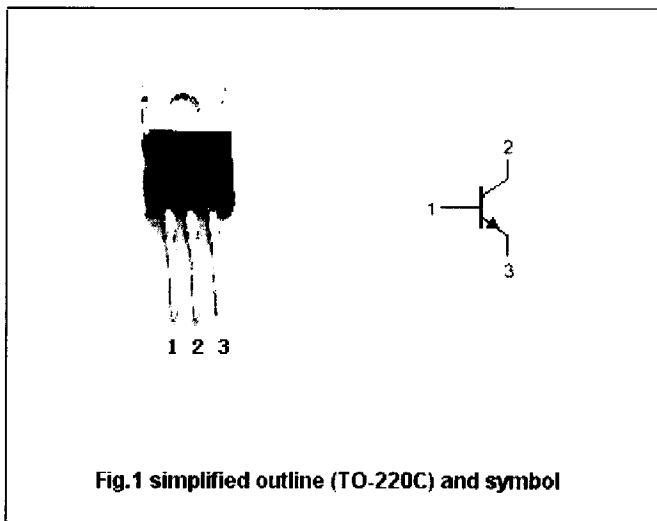


Fig.1 simplified outline (TO-220C) and symbol

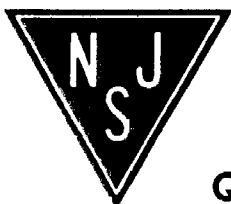
ABSOLUTE MAXIMUM RATINGS(T_C=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	450	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		5	A
I _B	Base current		1.5	A
P _C	Collector power dissipation	T _C =25	40	W
T _j	Junction temperature		150	-
T _{stg}	Storage temperature		-45~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-C}	Thermal resistance junction case	3.0	°W

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CHARACTERISTICS

T_J=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	450			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =0.1mA ; I _C =0	7			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.2	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =450V ; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =2 A ; V _{CE} =5V	10			

Switching times

t _{on}	Turn-on time	I _C =4A ; I _{B1} =0.8A I _{B2} =-0.8A ; R _L =20Ω			1.0	μs
t _s	Storage time				2.0	μs
t _f	Fall time				1.0	μs

